Rev. 2.1 — 24 July 2023

Product data sheet



1 General description

The P3A9606JK is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation for traditional I²C-bus/SMBus applications, 12.5 MHz I3C-bus applications and also higher speed SPI applications (with two devices). It features two 1-bit input-output ports (An and Bn), one output enable input (OE) and two supply pins (V_{CCA} and V_{CCB}). V_{CCA} can be supplied at any voltage between 0.72 V and 1.98 V and V_{CCB} can be supplied at any voltage between 0.72 V and 1.98 V, making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V and 1.8 V). V_{CCA} must be \leq V_{CCB} to ensure proper operation.

P3A9606JK can be used for both open drain as well as push-pull application which allows for level translation applications using I3C, I²C and SPI protocols.

Pins An are referenced to V_{CCA} and pins Bn are referenced to V_{CCB}. The active HIGH OE pin is referenced to V_{CCA} and controllable by a signal in either V_{CCA} or V_{CCB} domain. A LOW level at pin OE causes the outputs to be in a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.



2 Features and benefits

- Wide supply voltage range:
 - V_{CCA}: 0.72 V to 1.98 V and V_{CCB}: 0.72 V to 1.98 V; V_{CCA} \leq V_{CCB}
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 1.98 V and are overvoltage tolerant to 1.98 V
- Provided voltage level translation for I3C, I²C-bus, SMBus and SPI devices
- ESD protection:
 - HBM JESD22-A114E Class 2 exceeds 2000 V
- CDM JESD22-C101E exceeds 1000 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Available in X2SON8 package
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3 Ordering information

Table 1. Ordering information							
Type number		Package					
	marking	Name	Description	Version			
P3A9606JK	Tx ^[1]		super thin small outline package, no leads; 8 terminals; 0.35 mm pitch; 1.35 mm x 1.0 mm x 0.32 mm body	SOT2015-1			

[1] "x" changes based on date code.

3.1 Ordering options

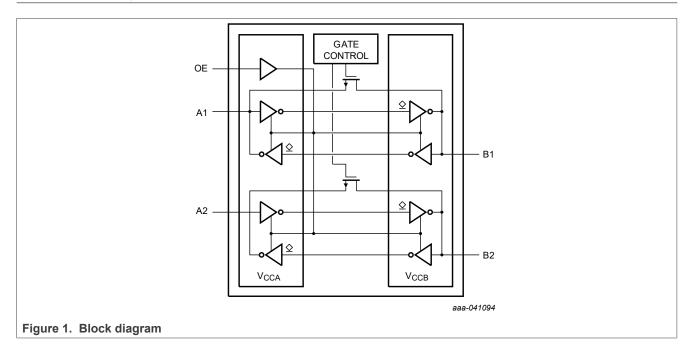
 Table 2. Ordering options

Type number	Orderable part number	Package	J	Minimum order quantity	Temperature
P3A9606JK	P3A9606JKZ		Reel 13" Q1/T1 *standard mark SMD with SSB ^[1]	20000	T_{amb} = -40 °C to +125 °C

[1] This packing method uses a Static Shielding Bag (SSB) solution. Material should be kept in the sealed bag between uses.

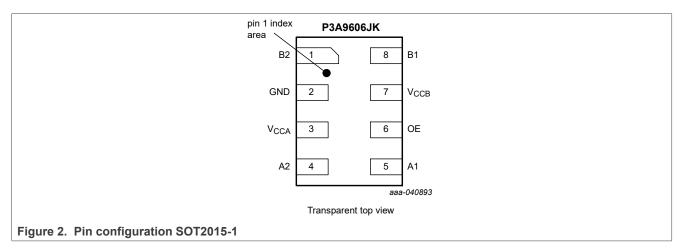
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4 Block diagram



5 Pinning information

5.1 Pinning



5.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B2, B1	1, 8	B port - data input or output (referenced to V _{CCB})
GND	2	ground (0 V)
V _{CCA}	3	supply voltage A
A2, A1	4, 5	A port - data input or output (referenced to V _{CCA})
OE	6	output enable input (active HIGH, referenced to V_{CCA}); signal can be from V_{CCA} or V_{CCB} domain
V _{CCB}	7	supply voltage B

Functional description 6

Table 4. Function table ^[1]

		Input	Input/output
V _{CCA}	V _{CCB}	OE ^[2]	
0.72 V to 1.98 V	0.72 V to 1.98 V	L	disconnected
0.72 V to 1.98 V	0.72 V to 1.98 V	Н	A1 = B1; A2 = B2
GND ^[3]	GND ^[3]	X	disconnected

[1]

H = HIGH voltage level; L = LOW voltage level; X = don't care V_{IL} and V_{IH} are referenced to V_{CCA} . The OE can be controlled by an external device that is powered by either V_{CCA} or V_{CCB} . As V_{CCB} is required to be greater than V_{CCA} , the OE pin has been designed to withstand a voltage equal to V_{CCB} (up to 1.98 V per recommended functional voltage range). When either V_{CCA} or V_{CCB} is at GND level, the device goes into Power-down mode. [2]

[3]

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Limiting values 7

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CCA}	supply voltage A	V _{CCA} ≤ V _{CCB}		-0.5	2.5	V
V _{CCB}	supply voltage B	V _{CCA} ≤ V _{CCB}		-0.5	2.5	V
VI	input voltage	A port, B port and OE	[1]	-0.5	2.5	V
Vo	output voltage	Active mode	[1][2][3]	-0.5	V _{CCO} + 0.25	V
		Power-down or 3-state mode	[1]	-0.5	2.5	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
I _O	output current	$V_{O} = 0 V$ to V_{CCO}	[2]	-	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}		-	100	mA
I _{GND}	ground current			-100	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C		-	125	mW

The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed. [1]

 V_{CCO} is the supply voltage associated with the output. V_{CCO} + 0.25 V should not exceed 2.5 V. [2] [3]

Recommended operating conditions 8

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CCA}	supply voltage A	$V_{CCA} \le V_{CCB}$	0.72	1.98	V
V _{CCB}	supply voltage B	$V_{CCA} \le V_{CCB}$	0.72	1.98	V
VI	input voltage	A port, B port and OE	0	1.98	V
Vo	output voltage	Power-down or 3-state mode; $V_{CCA} = 0.72 V \text{ to } 1.98 V$; $V_{CCB} = 0.72 V \text{ to } 1.98 V$			
		A port	0	1.98	V
		B port	0	1.98	V
T _{amb}	ambient temperature		-40	+125	°C
TJ	junction temperature ^[2]		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V	-	<5.3	ns/V

[1]

The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND. The T_J limits shall be supported by proper thermal PCB design taking the power consumption and the thermal resistance as listed in <u>Table 7</u> into account. [2]

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9 Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Value (typ)	Unit
R _{th(j-a)}	Thermal resistance from junction to ambient	X2SON8 package	114.9	°C/W
$\Psi_{(j-t)}$	Junction to top characterization	X2SON8 package	1.6	°C/W

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Static characteristics 10

Table 8. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{OH}	HIGH-level output voltage	A port; V _{CCA} = 1.2 V; I _O = -15 μA		-	1.05	-	V
V _{OL}	LOW-level output voltage	A port; V _{CCA} = 1.2 V; I _O = 20 μA	[1]	-	0.09	-	V
I _I	input leakage current	OE input; V _I = 0 V or 1.98 V; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	-	±1	μA
I _{OZ}	OFF-state output current	A or B port; V ₀ = 0 V to V _{CC0} ; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V	[2]	-	-	±1	μA
I _{OFF}	power-off leakage	A port; V_1 or $V_0 = 0$ V to 1.98 V; $V_{CCA} = 0$ V; $V_{CCB} = 0$ V to 1.98 V		-	-	±1	μA
	current	B port; V_1 or V_0 = 0 V to 1.98 V; V_{CCB} = 0 V; V_{CCA} = 0 V to 1.98 V		-	-	±1	μA
I _{CC}	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[3]				
		I _{CC(A)} ; V _{CCA} = 0.72 V; V _{CCB} = 0.72 V to 1.98 V		-	0.05	-	μA
		I _{CC(B)} ; V _{CCA} = 0.72 V; V _{CCB} = 0.72 V to 1.98 V		-	3.3	-	μA
		I _{CC(A)} + I _{CC(B)} ; V _{CCA} = 0.72 V; V _{CCB} = 0.72 V to 1.98 V		-	3.5	-	μA
CI	input capacitance	OE input; V_{CCA} = 0.72 V to 1.98 V; V_{CCB} = 0.72 V to 1.98 V		-	1.0	-	pF
C _{I/O}	input/output	A port; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	4.0	-	pF
	capacitance	B port; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	4.0	-	pF

When $V_I = 0.05 \text{ V}$, $I_O = 15 \ \mu\text{A}$, $R_{on(max)} = 250 \ \Omega$ ($V_{CCA} > 0.9 \text{ V}$), $R_{on(max)} = 370 \ \Omega$ ($V_{CCA} < 0.9 \text{ V}$), the low output voltage can be calculated as $V_{OL} = V_I + I_O * R_{on(max)}$ * $R_{on(max)}$ V_{CCO} is the supply voltage associated with the output. V_{CCI} is the supply voltage associated with the input. [1]

[2] [3]

Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).^[1]

Symbol	Parameter	Conditions		-40 °C to	o +85 °C	-40 °C to	+125 °C	Unit
				Min	Мах	Min	Мах	
V _{IH}	HIGH-level	A port or B port						
	input voltage	V _{CCA} = 0.72 V to 0.9 V; V _{CCB} = 0.72 V to 0.9 V	[1]	0.75V _{CCI}	-	0.75V _{CCI}	-	V
	V _{CCA} = 0.9 V to 1.98 V; V _{CCB} = 0.9 V to 1.98 V	[1]	0.7V _{CCI}	-	0.7V _{CCI}	-	V	
		OE input						
		V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		$0.65V_{CCA}$	-	0.65V _{CCA}	-	V
V _{IL}	LOW-level	A or B port						
	input voltage	V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	0.3V _{CCA}	-	0.3V _{CCA}	V
		OE input						
		V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	0.3V _{CCA}	-	0.3V _{CCA}	V

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Dual bidirectional I3C/I²C-bus and SPI voltage-level translator

Table 9. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).^[1]

Symbol	Parameter	Conditions		-40 °C to	o +85 ℃	-40 °C to	+125 °C	Unit
			-	Min	Max	Min	Мах	
V _{он}	HIGH-level	I _O = -15 μA	[2] [3]					
	output voltage	A port; V _{CCA} = 0.72 V to 1.98 V		V _{CCO} - 0.195	-	V _{CCO} - 0.195	-	V
		B port; V _{CCB} = 0.72 V to 1.98 V		V _{CCO} - 0.195	-	V _{CCO} - 0.195	-	V
V _{OL}	LOW-level	V _I = 0.05 V, I _O = 15 μA	[2] [4]					
	output voltage	A port; V _{CCA} = 0.72 V to 1.98 V		-	0.3	-	0.3	V
		B port; V _{CCB} = 0.72 V to 1.98 V		-	0.3	-	0.3	V
I	input leakage current OE input; VI = 0 V to 1.98 V; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V			-	±2	-	±5	μA
I _{OZ}	OFF-state output current	$\begin{array}{c} \text{(2)} \\ (2)$		-	±2	-	±10	μA
I _{OFF} power-off leakage current				-	±2	-	±10	μA
		B port; V _I or V _O = 0 V to 1.98 V; V _{CCB} = 0 V; V _{CCA} = 0 V to 1.98 V		-	±2	-	±10	μA
I _{CC} s	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[1]					
		I _{CC(A)}						
		OE = LOW; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	5	-	15	μA
		OE = HIGH; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	6	-	20	μA
		V _{CCA} = 1.98 V; V _{CCB} = 0 V		-	3.5	-	15	μA
		V _{CCA} = 0 V; V _{CCB} = 1.98 V		-	-2	-	-15	μA
		I _{CC(B)}						
		OE = LOW; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	8	-	29	μA
		OE = HIGH; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	11	-	36	μA
		V _{CCA} = 1.98 V; V _{CCB} = 0 V		-	-2	-	-15	μA
		V _{CCA} = 0 V; V _{CCB} = 1.98 V		-	6	-	20	μA
		$I_{CC(A)} + I_{CC(B)}$						
		OE = LOW; V _{CCA} = 0.72 V to 1.98 V; V _{CCB} = 0.72 V to 1.98 V		-	16	-	56	μA

[1] [2] [3]

 V_{CCI} is the supply voltage associated with the input. V_{CCO} is the supply voltage associated with the output. The V_{OH} min can be calculated by V_{CCO} - I_O x 10 kΩ x 1.3. The 1.3 factor is for the design margin. In this case, I_O = 15 µA and R_{UP} = 10 kΩ then V_{OH} min = V_{CCO} - 0.195 V.

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 $[4] \qquad When V_{I} = 0.05 \text{ V}, I_{O} = 15 \ \mu\text{A}, R_{on(max)} = 250 \ \Omega \ (V_{CCA} > 0.9 \text{ V}), R_{on(max)} = 370 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = V_{I} + I_{O} \\ * R_{on(max)} = 100 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{ V}), \text{ the low output voltage can be calculated as } V_{OL} = 0.00 \ \Omega \ (V_{CCA} < 0.9 \text{$

Dynamic characteristics 11

Table 10. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions		V _{CCB}			V _{CCB}		Unit
				1.2 V ± 10 %			1.8 V ± 10 %		
			Min	Тур	Max	Min	Тур	Max	
V _{CCA} = 0.8 \	V ± 10 %	1							
t _{pd}	propagation delay	A to B; C _L = 15 pF	2.1	5.6	7.7	1.7	3.9	5.3	ns
		B to A; C _L = 15 pF	1.2	10.6	19.9	0.5	9.6	17.2	ns
t _{en}	enable time	OE to A, B; C _L = 15 pF	16	125	150	16	120	160	ns
t _{dis} ^[2]	disable time	OE to A; no external load [3]	10		25	10		25	ns
		OE to B; no external load ^[3]	10		25	10		25	ns
		OE to A; C _L = 15 pF			50			50	ns
		OE to B; C _L = 15 pF			50			50	ns
t _t	transition time	A port; C _L = 15 pF	2.1	8.5	17.5	1.5	9	15.4	ns
		B port; C _L = 15 pF	1.1	4	5.8	0.7	1.5	2.1	ns
t _{sk(o)}	output skew time	delta between channels [4]	0	0.2	0.4	0	0.2	0.4	ns
w	pulse width	data inputs	37			37			ns
f _{data}	data rate		0.064		26	0.064		26	Mbps

 t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{en} is the same as t_{PZL} and t_{PZH} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_t is the same as t_{THL} and t_{TLH} . [1]

[2] Guaranteed by design.

Delay between OE going LOW and when the outputs are actually disabled. [3]

Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other. [4]

Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Symbol	Parameter	Conditions		V _{CCB}			V _{CCB}		Unit
			1.2 V ± 10 %				1.8 V ± 10 %		
			Min	Тур	Max	Min	Тур	Max	
V_{CCA} = 1.2	V ± 10 %						I		
t _{pd}	propagation delay	A to B; C _L = 15 pF	1.5	4.5	6.1	1.0	2.5	3.5	ns
		B to A; C _L = 15 pF	1.1	3.9	5.3	0.6	2.8	3.9	ns
t _{pdc} propagation delay	A to B; C _L = 80 pF	NA	NA	NA	2.5	4.9	7	ns	
	B to A; C _L = 30 pF	NA	NA	NA	0.9	3.4	5	ns	
t _{en}	enable time	OE to A, B; C _L = 15 pF	10	50	100	10	50	100	ns
t _{dis} ^[2] disal	disable time	OE to A; no external load ^[3]	10		25	10		25	ns
		OE to B; no external load ^[3]	10		25	10		25	ns
		OE to A; C _L = 15 pF			50	-		50	ns
		OE to B; C _L = 15 pF			50	-		50	ns
t _t	transition time	A port; C _L = 15 pF	0.8	2.6	3.5	0.6	1.5	2.5	ns
		B port; C _L = 15 pF	1.1	3.6	5.1	0.6	1.3	2.2	ns
t _{tc}	transition time	A port; C _L = 30 pF	NA	NA	NA	1.0	2.2	3.6	ns
		B port; C _L = 80 pF	NA	NA	NA	2.5	4.3	6.3	ns
t _{sk(o)}	output skew time	delta between channels [4]	0.0	0.1	0.2	0.0	0.1	0.3	ns
tw	pulse width	data inputs	15			13.5			ns
f _{data}	data rate		0.064		52	0.064		52	Mbps

 t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{en} is the same as t_{PZL} and t_{PZH} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_t is the same as t_{THL} and t_{TLH} . [1]

Guaranteed by design. Delay between OE going LOW and when the outputs are actually disabled. [2] [3] [4]

Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

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Symbol	Parameter	Conditions		V _{CCB}		Unit	
				1.8 V ± 10 %			
			Min	Тур	Max		
V _{CCA} = 1.8 V ±	10 %	·	·			·	
t _{pd}	propagation delay	A to B; C _L = 15 pF	1	2.5	3.4	ns	
		B to A; C _L = 15 pF	0.7	2.3	3	ns	
t _{en}	enable time	OE to A, B; C _L = 15 pF	8	25	50	ns	
t _{dis} ^[2]	disable time	OE to A; no external load ^[3]	10		25	ns	
		OE to B; no external load ^[3]	10		25	ns	
		OE to A; C _L = 15 pF			50	ns	
		OE to B; C _L = 15 pF			50	ns	
t _t	transition time	A port; C _L = 15 pF	0.5	1.2	1.7	ns	
		B port; C _L = 15 pF	0.7	1.7	2.5	ns	
t _{sk(o)}	output skew time	delta between channels [4]	0	0.1	0.2	ns	
t _W	pulse width	data inputs	13.5			ns	
f _{data}	data rate		0.064		52	Mbps	

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

t_{pd} is the same as t_{PLH} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}. Guaranteed by design. [1] [2]

Delay between OE going LOW and when the outputs are actually disabled. [3]

[4] Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveform see Figure 3.

Parameter	Conditions	V _{CCB}			V _{CCB}			Unit
		1.2 V ± 10 %			1.8 V ± 10 %			7
		Min	Тур	Мах	Min	Тур	Мах	1
± 10 %								
propagation delay	A to B; C _L = 15 pF	2.1	5.6	7.7	1.7	3.9	5.3	ns
	B to A; C _L = 15 pF	1.2	10.6	19.9	0.5	9.6	17.2	ns
enable time	OE to A, B; C _L = 15 pF	16	125	150	16	120	160	ns
disable time	OE to A; no external load ^[3]	10		25	10		25	ns
	OE to B; no external load [3]	10		25	10		25	ns
	OE to A; C _L = 15 pF			50			50	ns
	OE to B; C _L = 15 pF			50			50	ns
transition time	A port; C _L = 15 pF	2.1	8.5	17.5	1.5	9	15.4	ns
	B port; C _L = 15 pF	1.1	4	5.8	0.7	1.5	2.1	ns
output skew time	delta between channels [4]	0	0.2	0.4	0	0.2	0.4	ns
pulse width	data inputs	37			37			ns
data rate		0.064		26	0.064		26	Mbps
	± 10 % propagation delay enable time disable time transition time output skew time pulse width		$ \begin{array}{ c c c c c } \hline \hline \\ $	$ \begin{array}{ c c c c } \hline 1.2 \ V \pm 10 \ \% \\ \hline 1.2 \ V \pm 10 \ \% \\ \hline \ 1.2 \ V \pm 10 \ \% \\ \hline \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	$ \begin{array}{ c c c c } \hline \begin{tabular}{ c c c } \hline \begin{tabular}{ c c c } \hline \hline \end{tabular} \\ \hline \hline \end{tabular} \\ \hline \hline \end{tabular} \\ \hline t$	$ \begin{array}{ c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	$ \begin{array}{ c c c c c c } \hline c c c c c c c c c c c c c c c c c c $	$ \begin{array}{ c c c c c c } \hline \begin{tabular}{ c c c c } \hline \begin{tabular}{ c c c c c c } \hline \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$

 t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{en} is the same as t_{PZL} and t_{PZH} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_t is the same as t_{THL} and t_{TLH} . Guaranteed by design. [1]

[2]

[3] [4] Delay between OE going LOW and when the outputs are actually disabled.

Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other.

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions	V _{CCB}	V _{CCB}		V _{CCB}	Unit		
			1.2 V ± 10 %		1.8 V ± 10 %				
			Min	Тур	Max	Min	Тур	Max	
V_{CCA} = 1.2 V ± 7	10 %								
t _{pd}	propagation delay	A to B; C _L = 15 pF	1.5	4.5	6.2	1.0	2.5	3.6	ns
		B to A; C _L = 15 pF	1.1	3.9	5.4	0.6	2.8	4.0	ns

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Symbol	Parameter	Conditions	V _{CCB}			V _{CCB}			Unit
			1.2 V ± 10	1.2 V ± 10 %			1.8 V ± 10 %		
			Min	Тур	Max	Min	Тур	Мах	
t _{pdc}	propagation delay	A to B; C _L = 80 pF	NA	NA	NA	2.5	4.9	7.4	ns
		B to A; C _L = 30 pF	NA	NA	NA	0.9	3.4	5.3	ns
t _{en}	enable time	OE to A, B; C _L = 15 pF	10	50	100	10	50	100	ns
t _{dis} ^[2]	disable time	OE to A; no external load ^[3]	10		25	10		25	ns
		OE to B; no external load ^[3]	10		25	10		25	ns
		OE to A; C _L = 15 pF			50	-		50	ns
		OE to B; C _L = 15 pF			50	-		50	ns
t _t	transition time	A port; C _L = 15 pF	0.8	2.6	3.5	0.6	1.5	2.6	ns
		B port; C _L = 15 pF	1.1	3.6	5.1	0.6	1.3	2.3	ns
t _{tc}	transition time	A port; C _L = 30 pF	NA	NA	NA	1.0	2.2	3.8	ns
		B port; C _L = 80 pF	NA	NA	NA	2.5	4.3	6.9	ns
t _{sk(o)}	output skew time	delta between channels [4]	0	0.1	0.2	0	0.1	0.3	ns
t _W	pulse width	data inputs	15			13.5			ns
f _{data}	data rate		0.064		52	0.064		52	Mbps

Table 14. Dynamic characteristics for temperature range -40 °C to +125 °C [1]...continued Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

t_{pd} is the same as t_{PLL} and t_{PHL}; t_{en} is the same as t_{PZL} and t_{PZH}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_t is the same as t_{THL} and t_{TLH}. Guaranteed by design. [1]

[2]

[3]

Delay between OE going LOW and when the outputs are actually disabled. Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other. [4]

Table 15. Dynamic characteristics for temperature range -40 °C to +125 °C ^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 4; for waveforms see Figure 3 and Figure 4.

Symbol	Parameter	Conditions		V _{CCB} 1.8 V ± 10 %			
			Min	Тур	Max		
V _{CCA} = 1.8 V ±	: 10 %		l.	·	L	L	
t _{pd}	propagation delay	A to B; C _L = 15 pF	1	2.5	3.5	ns	
		B to A; C _L = 15 pF	0.7	2.3	3.1	ns	
t _{en}	enable time	OE to A, B; C _L = 15 pF	8	25	50	ns	
t _{dis} ^[2]	disable time	OE to A; no external load ^[3]	10		25	ns	
		OE to B; no external load ^[3]	10		25	ns	
		OE to A; C_L = 15 pF			50	ns	
		OE to B; C_L = 15 pF			50	ns	
tt	transition time	A port; C _L = 15 pF	0.5	1.2	1.7	ns	
		B port; C _L = 15 pF	0.7	1.7	2.6	ns	
t _{sk(o)}	output skew time	delta between channels ^[4]	0	0.1	0.2	ns	
t _W	pulse width	data inputs	13.5			ns	
f _{data}	data rate		0.064		52	Mbps	

 t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{en} is the same as t_{PZL} and t_{PZH} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_t is the same as t_{THL} and t_{TLH} . Guaranteed by design. Delay between OE going LOW and when the outputs are actually disabled. Skew between any two outputs of the same package switching in the same direction. One channel is not always faster than the other. [1]

[2] [3] [4]

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12 Waveforms

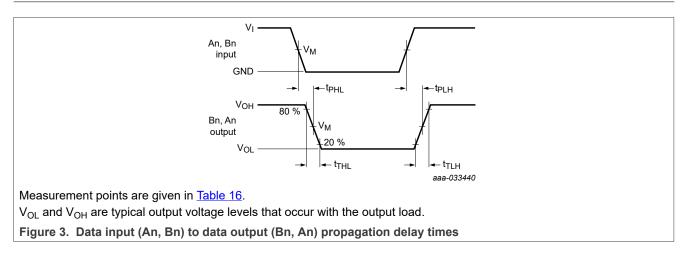


Table 16. Measurement points

 V_{CCI} is the supply voltage associated with the input and V_{CCO} is the supply voltage associated with the output.

Supply voltage	Input	Output		
V _{cco}	V _M	V _M	V _X	V _Y
0.8 V ± 10 %	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.08 V	V _{OH} - 0.08 V
1.2 V ± 10 %	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.12 V	V _{OH} - 0.12 V
1.8 V ± 10 %	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.18 V	V _{OH} - 0.18 V

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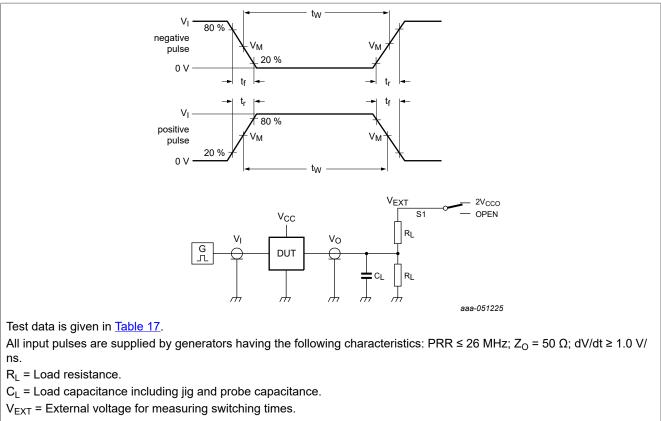


Figure 4. Test circuit for measuring switching times

Table	17.	Test	data	

Supply voltage	ply voltage Input			Load		V _{EXT}		
V _{CCA}	V _{CCB}	V _I ^[1]	Δt/ΔV	CL	R _L ^[2]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t_{PZL}, t_{PLZ} ^[3]
0.72 V to 1.98 V	0.72 V to 1.98 V	V _{CCI}	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}

[1] V_{CCI} is the supply voltage associated with the input.

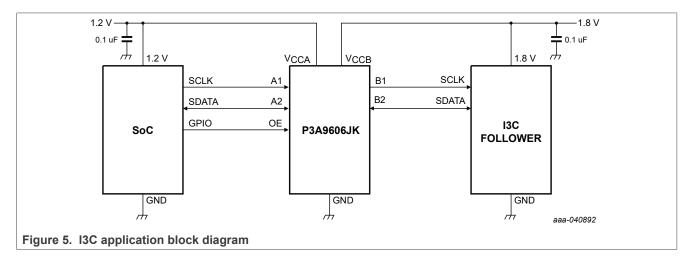
[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, $R_L = 1 M\Omega$; for measuring enable and disable times, $R_L = 50 k\Omega$.

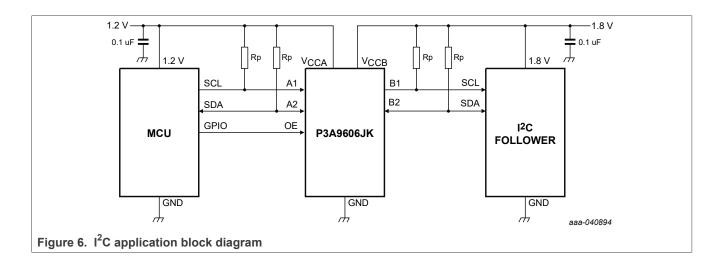
[3] V_{CCO} is the supply voltage associated with the output.

13 Application information

13.1 Applications

Voltage level-translation applications. The P3A9606JK can be used to interface between devices or systems operating at different supply voltages. See <u>Figure 5</u>, <u>Figure 6</u>, <u>Figure 7</u> and <u>Figure 8</u> for a typical operating circuit using the P3A9606JK.





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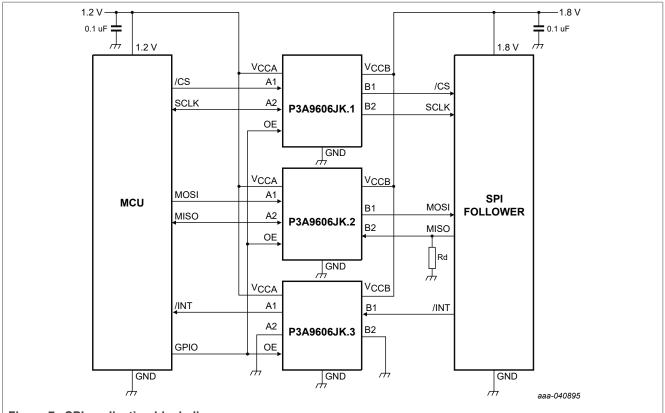
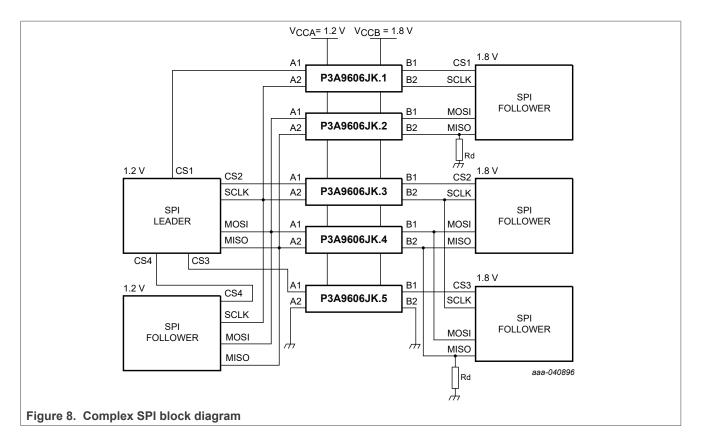


Figure 7. SPI application block diagram

Dual bidirectional I3C/I²C-bus and SPI voltage-level translator



13.2 Architecture

The architecture uses edge-rate accelerator circuitry (for both the high-to-low and low-to-high), N-Channel Pass gate transistor and a pull-up resistor (to provide DC-bias and drive capabilities) to meet these requirements. The design is directionless and does not need direction control signal. The implementation supports both low speed Open-drain operation as well as high speed push-pull operation. The N-Channel Pass device will be on only during Low input cycle and will be off during High input cycle.

13.3 Input driver requirements

The continuous DC- current sinking or sourcing capability is determined by the external system-level; opendrain or push-pull drivers that are interfaced to the P3A9606JK IO pins.

The high bandwidth of these IO circuits used to facilitate this fast change from an input to an output and an output to an input, they have a modest sourcing capability of hundreds of micro-amperes, as determined by the pull-up resistor.

The fall time of a signal depends on the edge-rate and output impedance of the external driving the P3A9606JK data IOs, as well as the capacitive loading at the data lines.

13.4 Power up and power down

13.4.1 Power-up sequence

Turn on V_{CCB} first to recommended operating voltage range, then turn on V_{CCA} .

13.4.2 Power-down sequence

Turn off V_{CCB} first, and after it is completely off then turn off V_{CCA} . The different sequencing of each power supply will not damage the device during the power up operation.

The P3A9606JK includes circuitry that disables all output ports and puts the device into a power-down mode when either V_{CCA} or V_{CCB} is switched off.

13.5 Enable and disable

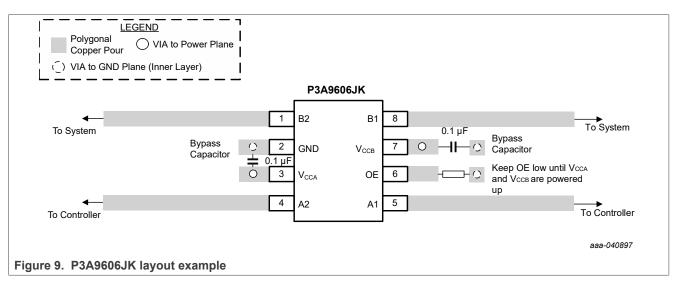
An output enable input (OE) is used to enable/disable the device when both V_{CCA} and V_{CCB} are in recommended operating conditions. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power up or power down, pin OE should be tied to GND, OE pin should not be left floating in any condition.

OE V_{IL} and V_{IH} are referenced to V_{CCA} . The OE can be controlled by an external device that is powered by either V_{CCA} or V_{CCB} . As V_{CCB} is required to be greater than V_{CCA} , the OE pin has been designed to withstand a voltage equal to V_{CCB} (up to 1.98 V per recommended functional voltage range).

13.6 Layout guidelines

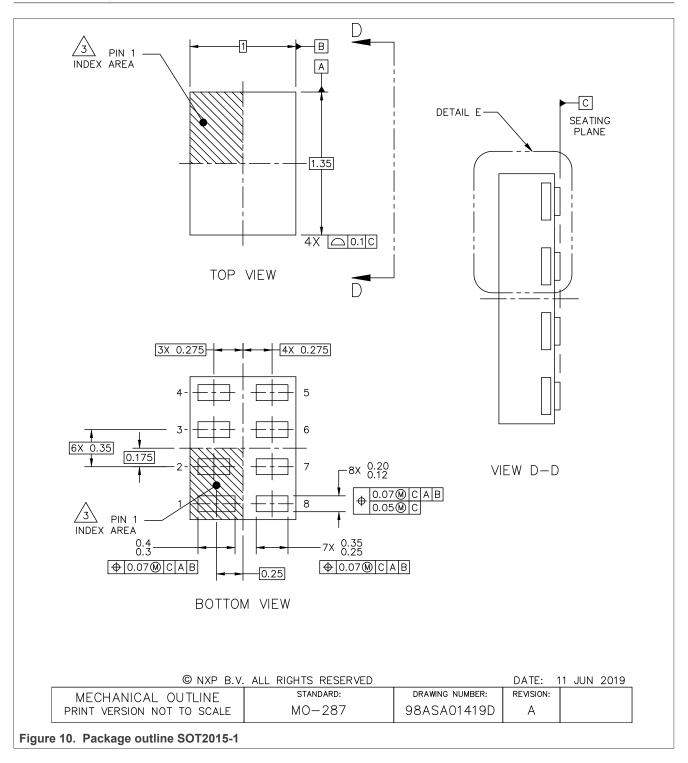
To ensure reliability of the device, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors should be used on power supplies and should be placed as close as possible to V_{CCA} , V_{CCB} , and GND pins.
- · Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one-shot duration, approximately 8 ns, ensuring that any reflection encounters low impedance at the source driver.



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14 Package outline

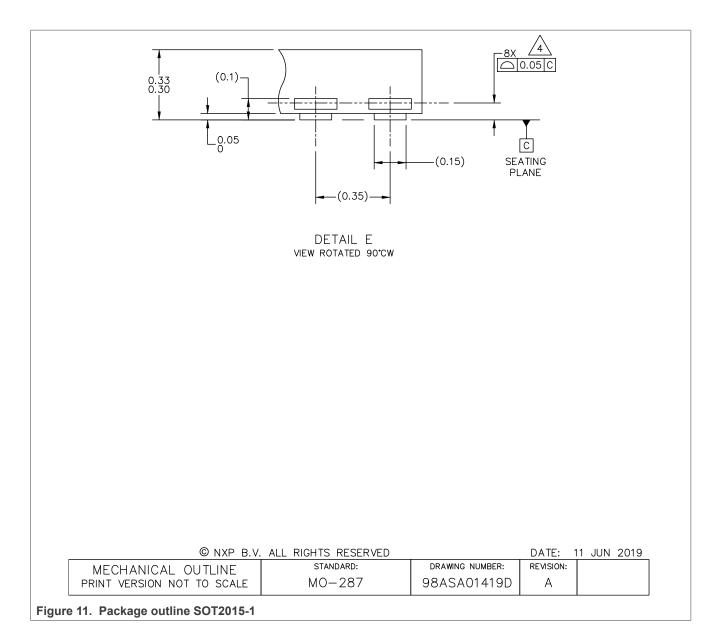


Product data sheet

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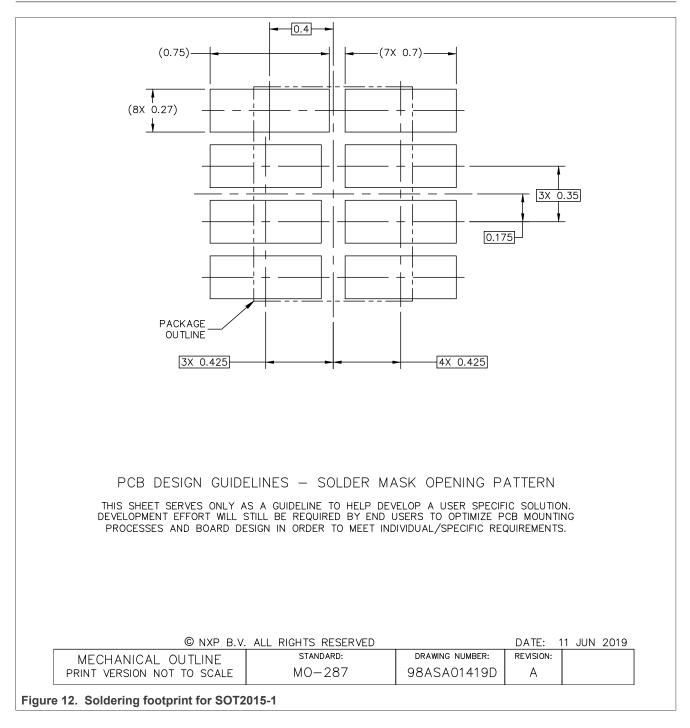
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Dual bidirectional I3C/I²C-bus and SPI voltage-level translator

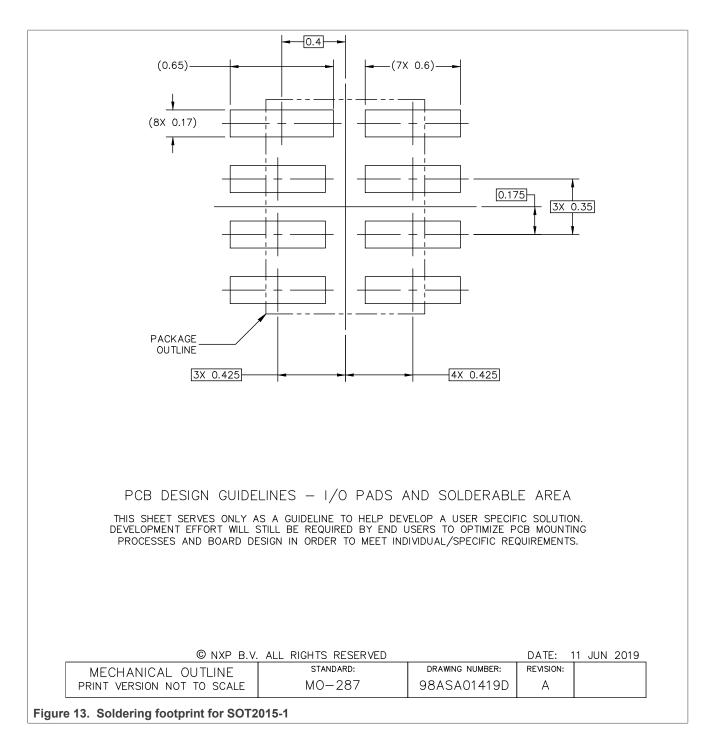
15 Soldering



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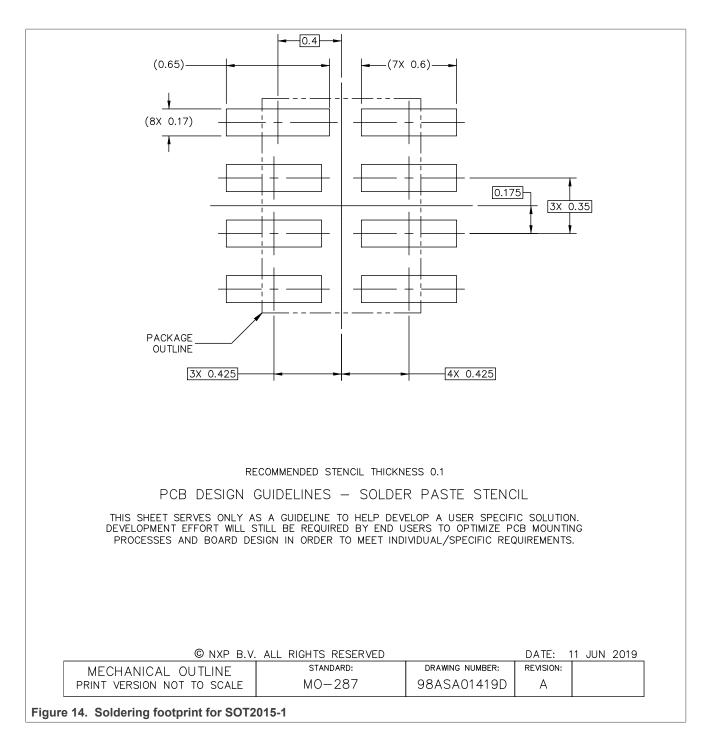
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Product data sheet

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	NOTES:				
	1. ALL DIMENSIONS ARE I	N MILLIMETERS.			
	2. DIMENSIONING AND TO	_ERANCING PER ASME Y14.5M	<i>I</i> —1994.		
	^	, SIZE AND LOCATION MAY \			
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	5. MIN METAL GAP SHOU				
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16 Abbreviations

Table 18. Abbre	Table 18. Abbreviations					
Acronym	Description					
CDM	Charged Device Model					
DUT	Device Under Test					
ESD	ElectroStatic Discharge					
НВМ	Human Body Model					
MM	Machine Model					
NMOS	N-type Metal Oxide Semiconductor					
PMOS	P-type Metal Oxide Semiconductor					
PRR	Pulse Repetition Rate					

17 Revision history

Document ID	Release date	Description				
P3A9606JK v.2.1	24 July 2024	 Updated per CIN 202407007I: <u>Section 13.4</u>, <u>Section 13.5</u>: Clarified V_{CCA} and V_{CCB} operating conditions 				
P3A9606JK v.2.0	4 January 2023	 Updated per CIN 202212010I: <u>Table 8</u>: Updated V_{OH} and V_{OL} conditions and logic levels to meet I3C spec. <u>Table 9</u>: Updated V_{IH} min values for V_{CCA} = 0.9 V to 1.98 V; V_{CCB} = 0.9 V to 1.98 V. 				
P3A9606JK v.1.0	5 October 2021	Initial version				

Table 19. Revision history

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Dual bidirectional I3C/I²C-bus and SPI voltage-level translator

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Document feedback Date of release: 24 July 2023 Document identifier: P3A9606JK